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(54) Title: CRUCIBLE FOR THE PRODUCTION OF CRYSTALLINE SEMICONDUCTOR INGOTS AND PROCESS FOR MANUFACTURING THE SAME

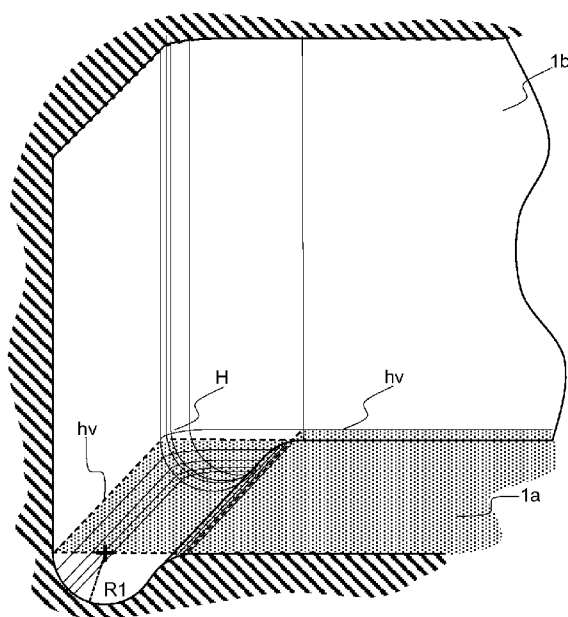


FIGURE 3

(57) Abstract: The present invention concerns a crucible (1) for the production of crystalline semiconductor ingots, said crucible comprising an inner volume defined by a floor (1a) which top surface comprises a planar portion defining a first horizontal plane (H) and peripheral side walls (1b) each comprising an inner surface comprising a planar portion substantially vertical, defining a substantially vertical plane (V), and normal to the first, horizontal plane (H), said side walls (1b) joining the floor (1a) at the perimeter of the latter by forming a radius of curvature, R1, of at least 1 mm, characterized in that, the intersecting line (hv) forming the intersection between the first, horizontal plane (H) and the substantially vertical planes (V) defined by the substantially vertical planar portions of each side wall (1b) is entirely located on the side walls (1b), on the floor (1a), or in the inner volume of the crucible.

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